Pawel Podemski

List of Publications by Citations

34 papers	350 citations	11 h-index	17 g-index
41 ext. papers	387 ext. citations	2.8 avg, IF	2.59 L-index

#	Paper	IF	Citations
34	Carrier trapping and luminescence polarization in quantum dashes. *Physical Review B*, **2012**, 85,	3.3	34
33	Photoreflectance-probed excited states in InAs/InGaAlAs quantum dashes grown on InP substrate. *Applied Physics Letters*, **2006**, 89, 031908	3.4	32
32	Measurement of an exciton Rabi rotation in a single GaN/Al(x)Ga(1-x)N nanowire-quantum dot using photoluminescence spectroscopy: evidence for coherent control. *Physical Review Letters*, **2013**, 111, 057401	7.4	25
31	Experimental evidence on quantum well/quantum dash energy transfer in tunnel injection structures for 1.55μm emission. *Applied Physics Letters*, **2007**, 90, 081915	3.4	24
30	Thermal quenching of photoluminescence from InAs/In0.53Ga0.23Al0.24As/InP quantum dashes with different sizes. *Applied Physics Letters*, **2006**, 89, 151902	3.4	21
29	Columnar quantum dashes for an active region in polarization independent semiconductor optical amplifiers at 1.55μm. *Applied Physics Letters*, **2008**, 93, 171910	3.4	19
28	Photoluminescence from a single InGaAs epitaxial quantum rod. *Applied Physics Letters*, **2008**, 92, 021901	3.4	18
27	On the tunnel injection of excitons and free carriers from In0.53Ga0.47As/In0.53Ga0.23Al0.24As quantum well to InAs/In0.53Ga0.23Al0.24As quantum dashes. *Applied Physics Letters*, **2006**, 89, 061902	3.4	15
26	Height-driven linear polarization of the surface emission from quantum dashes. *Semiconductor Science and Technology*, **2012**, 27, 105022	1.8	12
25	Orientation dependent emission properties of columnar quantum dash laser structures. *Applied Physics Letters*, **2009**, 94, 241113	3.4	12
24	Photoluminescence Excitation Spectroscopy on Single GaN Quantum Dots. *Applied Physics Express*, **2013**, 6, 012102	2.4	11
23	Hole Subband Mixing and Polarization of Luminescence from Quantum Dashes: A Simple Model. *Acta Physica Polonica A*, **2011**, 119, 633-636	0.6	11
22	On the applicability of a few level rate equation model to the determination of exciton versus biexciton kinetics in quasi-zero-dimensional structures. *Journal of Applied Physics*, **2010**, 108, 033507	2.5	10
21	Probing the excitonic states of site-controlled GaN nanowire quantum dots. *Nano Letters*, **2015**, 15, 1047-51	11.5	9
20	Single dot photoluminescence excitation spectroscopy in the telecommunication spectral range. *Journal of Luminescence*, **2019**, 212, 300-305	3.8	6
19	Interplay between emission wavelength and s-p splitting in MOCVD-grown InGaAs/GaAs quantum dots emitting above 1.3 μm. *Applied Physics Letters*, **2020**, 116, 023102	3.4	6
18	Temperature Dependent Photoluminescence Excitation Spectroscopy of GaN Quantum Dots in Site Controlled GaN/AlGaN Nanowires. *Japanese Journal of Applied Physics*, **2013**, 52, 08JL02	1.4	6

17	On the mechanisms of energy transfer between quantum well and quantum dashes. *Journal of Applied Physics*, **2012**, 112, 033520	2.5	6
16	Excited states of neutral and charged excitons in single strongly asymmetric InP-based nanostructures emitting in the telecom C band. *Physical Review B*, **2019**, 100,	3.3	6
15	Temperature Dependence of Photoluminescence from Epitaxial InGaAs/GaAs Quantum Dots with High Lateral Aspect Ratio. *Acta Physica Polonica A*, **2011**, 120, 883-887	0.6	5
14	Optimizing the InGaAs/GaAs Quantum Dots for 1.3 □n Emission. *Acta Physica Polonica A*, **2017**, 132, 386-390	0.6	5
13	Immersion Layer in Columnar Quantum Dash Structure as a Polarization Insensitive Light Emitter at 1.55 □m. *Applied Physics Express*, **2009**, 2, 061102	2.4	4
12	Optically pumped lasing from a single pillar microcavity with InGaAs/GaAs quantum well potential fluctuation quantum dots. *Journal of Applied Physics*, **2009**, 105, 053513	2.5	3
11	Efficient energy transfer in InAs quantum dash based tunnel-injection structures at low temperatures **2007**,		3
10	Multiexcitonic emission from single elongated InGaAs/GaAs quantum dots. *Journal of Applied Physics*, **2012**, 111, 063522	2.5	2
9	Electromodulation spectroscopy of In0.53Ga0.47As/In0.53Ga0.23Al0.24As quantum wells. *Superlattices and Microstructures*, **2009**, 46, 425-434	2.8	2
8	Excitonic complexes in InGaAs/GaAs quantum dash structures. *Journal of Physics: Conference Series*, **2010**, 245, 012054	0.3	2
7	Energy Transfer Processes in InAs/GaAs Quantum Dot Bilayer Structure. *Acta Physica Polonica A*, **2016**, 129, A-59-A-61	0.6	2
6	Spin memory effect in charged single telecom quantum dots. *Optics Express*, **2021**, 29, 34024-34034	3.3	2
5	GaAs-Based Quantum Well Exciton-Polaritons beyond 1 □n. *Acta Physica Polonica A*, **2013**, 124, 817-820	0.6	1
4	Contactless modulated reflectivity of quasi 0D self-assembled semiconductor structures. *Physica Status Solidi (A) Applications and Materials Science*, **2007**, 204, 400-411	1.6	1
3	Probing the carrier transfer processes in a self-assembled system with In0.3Ga0.7As/GaAs quantum dots by photoluminescence excitation spectroscopy. *Superlattices and Microstructures*, **2016**, 93, 214-220	2.8	
2	Electronic Structure of Elongated In_{0.3}Ga_{0.7}As/GaAs Quantum Dots. *Acta Physica Polonica A*, **2013**, 124, 809-812	0.6	
1	Spin memory effect in charged single telecom quantum dots: erratum. *Optics Express*, **2021**, 29, 36460	3.3	